

## Product Summary

BV <sub>DSS</sub>	R <sub>DSON</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-30V	7.5mΩ @ V <sub>GS</sub> = -10V	-36A
	10mΩ @ V <sub>GS</sub> = -4.5V	-31A

## Description

This new generation 30V P-Channel Enhancement Mode MOSFET is designed to minimize R<sub>DSON</sub>, yet maintain superior switching performance. This device is ideal for use in notebook battery power management and loadswitch.

## Applications

- Notebook Battery Power Management
- DC-DC Converters
- Loadswitch

## Features

- Thermally Efficient Package – Cooler Running Applications
- High Conversion Efficiency
- Low R<sub>DSON</sub> – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile – Ideal for Thin Applications
- ESD HBM Protected up to 1kV
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet ([DMP3010LPSQ](#))

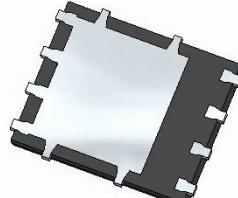
## Mechanical Data

- Case: PowerDI® 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish – 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.097 grams (Approximate)

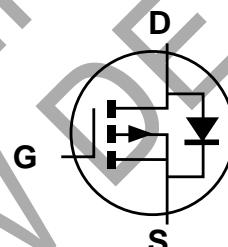
PowerDI5060-8



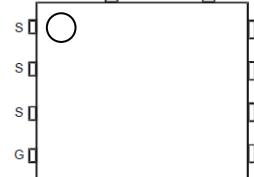
Top View



Bottom View



Internal Schematic



Top View  
Pin Configuration

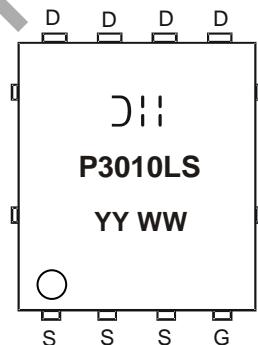
## Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP3010LPS-13	Standard	PowerDI5060-8	2,500/Tape & Reel

Notes:

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



DII = Manufacturer's Marking  
P3010LS = Product Type Marking Code  
YYWW = Date Code Marking  
YY = Year (ex: 17 = 2017)  
WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

DMP3010LPS

Document number: DS32239 Rev. 13 - 3

## Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 7) $V_{GS} = -10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	-36 -29	A
Continuous Drain Current (Note 7) $V_{GS} = -4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	-31 -25	A
Continuous Drain Current (Note 6) $V_{GS} = -10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	-14.5 -11.5	A
Pulsed Drain Current (Notes 6 & 9)			$I_{DM}$	-100	A
Avalanche Current (Notes 10 & 11)			$I_{AS}$	-17.5	A
Avalanche Energy (Notes 10 & 11) $L = 1\text{mH}$			$E_{AS}$	153	mJ

## Thermal Characteristics

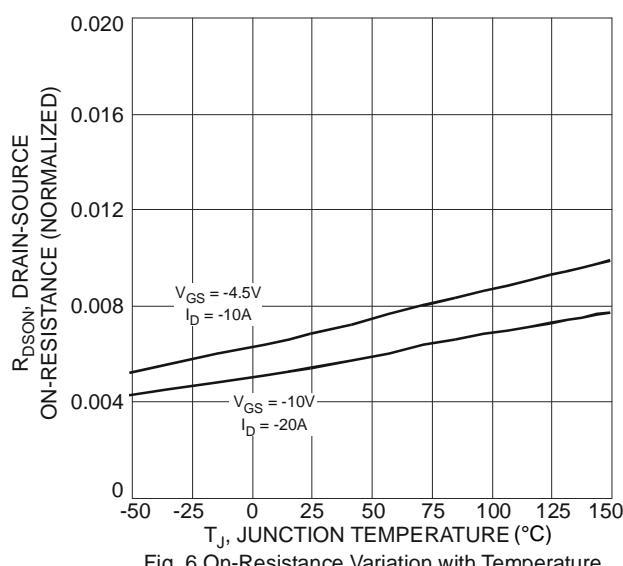
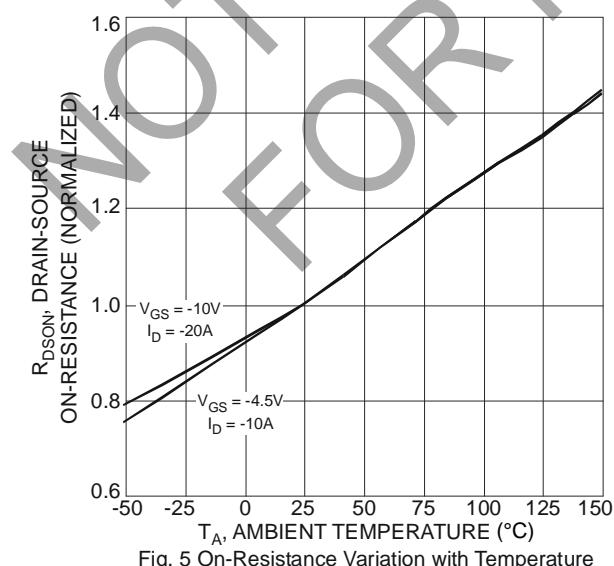
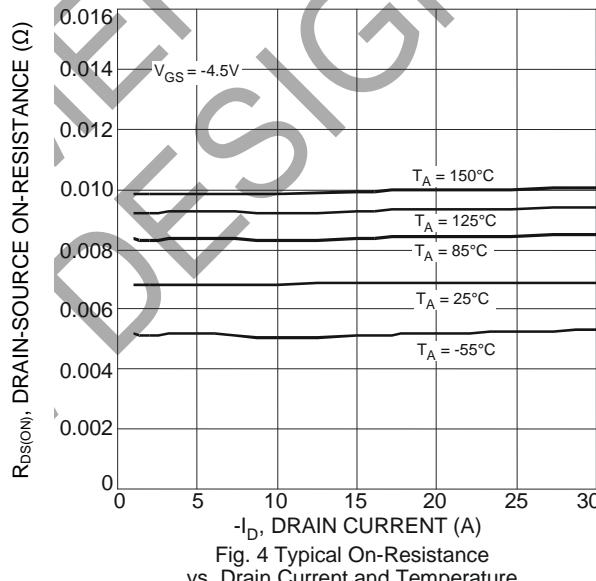
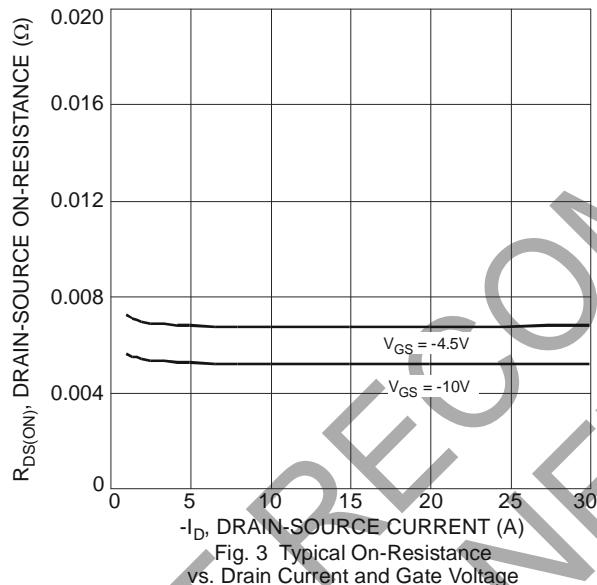
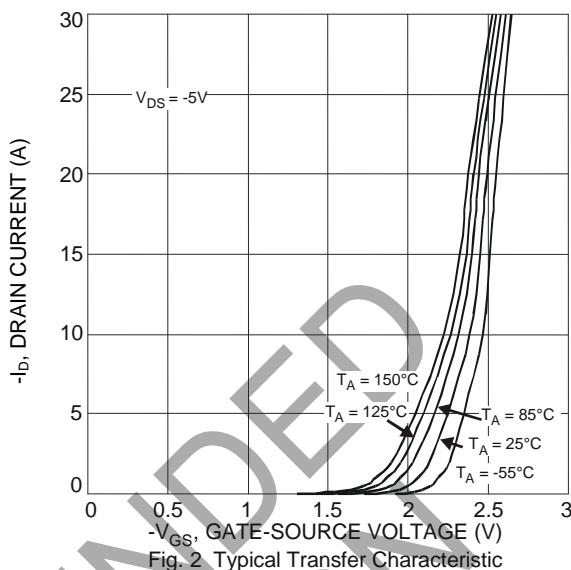
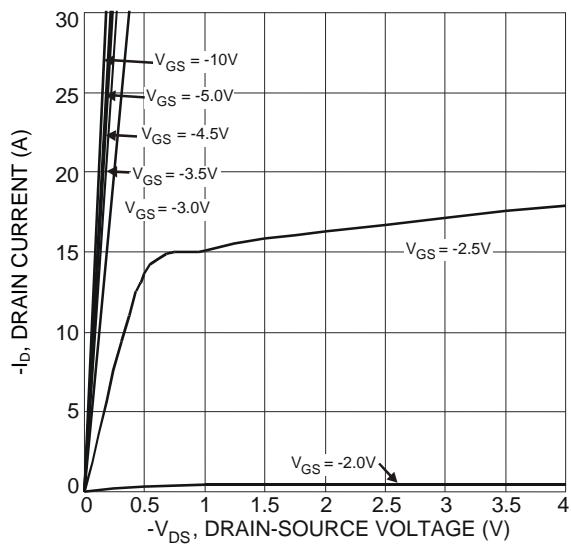
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_D$	1.26	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	97	$^\circ\text{C}/\text{W}$
Power Dissipation (Note 6)	$P_D$	2.18	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 6)	$R_{\theta JA}$	55	$^\circ\text{C}/\text{W}$
Power Dissipation (Note 7)	$P_D$	14.37	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 7)	$R_{\theta JA}$	8.7	$^\circ\text{C}/\text{W}$
Power Dissipation (Notes 7 & 8)	$P_D$	58.7	W
Thermal Resistance, Junction to Case @ $T_C = +25^\circ\text{C}$ (Notes 7 & 8)	$R_{\theta JC}$	2.13	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

## Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 11)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-30	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	-1.0	$\mu\text{A}$	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 11)</b>						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	-1.1	-1.6	-2.1	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	5.7	7.5	$\text{m}\Omega$	$V_{GS} = -10\text{V}, I_D = -10\text{A}$
		—	7.2	10		$V_{GS} = -4.5\text{V}, I_D = -10\text{A}$
Forward Transfer Admittance	$ Y_{fs} $	—	30	—	S	$V_{DS} = -15\text{V}, I_D = -10\text{A}$
Diode Forward Voltage	$V_{SD}$	—	-0.65	-1.0	V	$V_{GS} = 0\text{V}, I_S = -1\text{A}$
<b>DYNAMIC CHARACTERISTICS (Note 12)</b>						
Input Capacitance	$C_{iss}$	—	6,234	—	$\text{pF}$	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	—	1,500	—	$\text{pF}$	
Reverse Transfer Capacitance	$C_{rss}$	—	774	—	$\text{pF}$	
Gate Resistance	$R_g$	—	1.28	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ( $V_{GS} = -10\text{V}$ )	$Q_g$	—	126.2	—	nC	$V_{DS} = -15\text{V}, I_D = -10\text{A}$
Total Gate Charge ( $V_{GS} = -4.5\text{V}$ )	$Q_g$	—	59.2	—	nC	$V_{DS} = -15\text{V}, V_{GS} = -4.5\text{V}, I_D = -10\text{A}$
Gate-Source Charge	$Q_{gs}$	—	16.1	—	nC	
Gate-Drain Charge	$Q_{gd}$	—	15.7	—	nC	
Turn-On Delay Time	$t_{D(\text{ON})}$	—	11.4	—	ns	$V_{DS} = -15\text{V}, V_{GEN} = -10\text{V}, R_G = 6\Omega, I_D = -1\text{A}$
Turn-On Rise Time	$t_R$	—	9.4	—	ns	
Turn-Off Delay Time	$t_{D(\text{OFF})}$	—	260.7	—	ns	
Turn-Off Fall Time	$t_F$	—	99.3	—	ns	

Notes:

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Device mounted on FR-4 PCB with infinite heatsink.
8.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.
9. Repetitive rating, pulse width limited by junction temperature, 10s pulse, duty cycle = 1%.
10.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^\circ\text{C}$ .
11. Short duration pulse test used to minimize self-heating effect.
12. Guaranteed by design. Not subject to product testing.



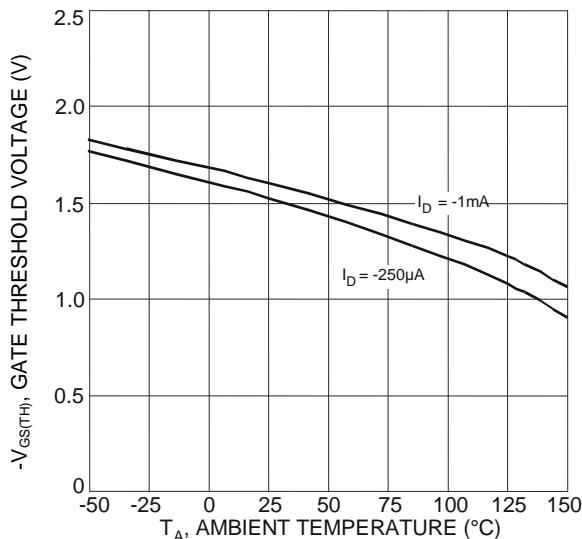


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

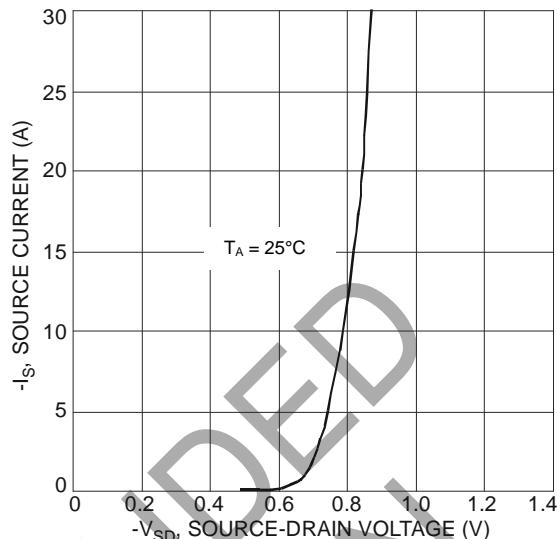


Fig. 8 Diode Forward Voltage vs. Current

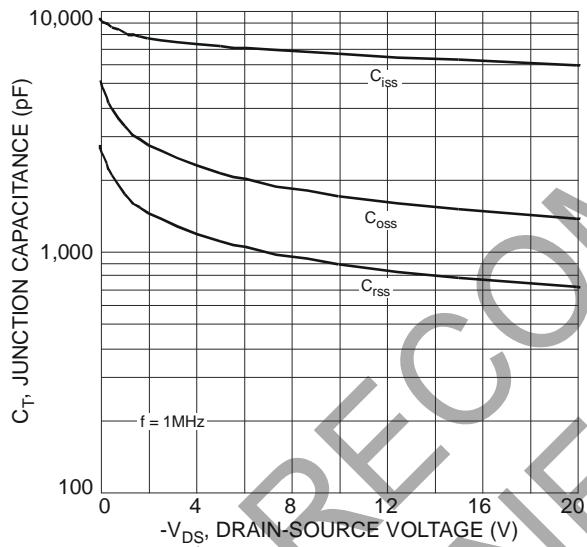


Fig. 9 Typical Total Capacitance

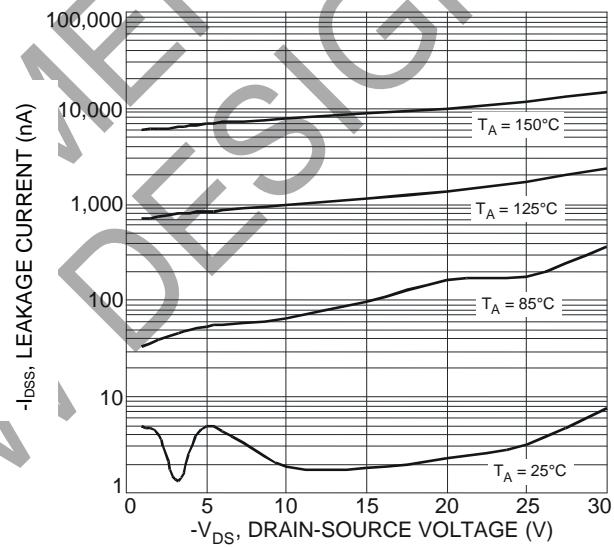


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

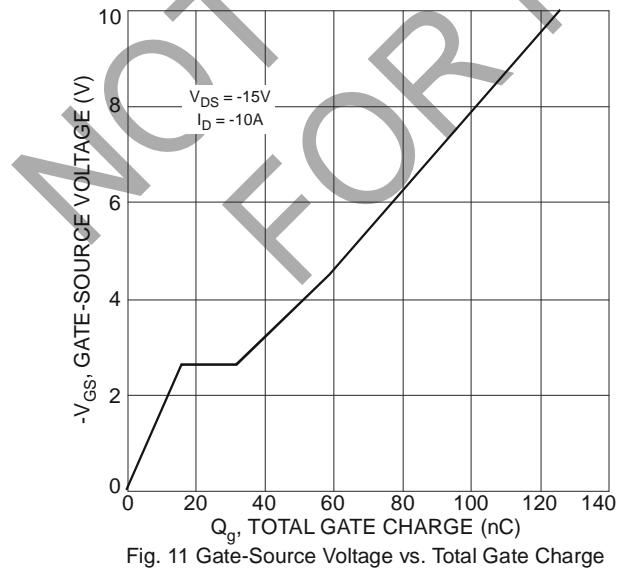


Fig. 11 Gate-Source Voltage vs. Total Gate Charge

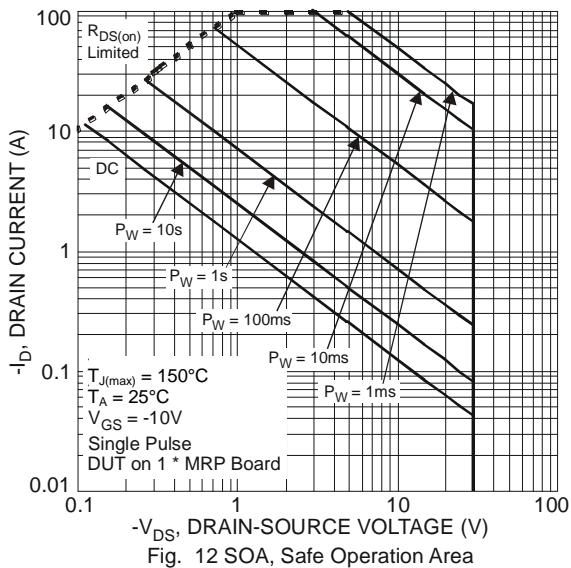
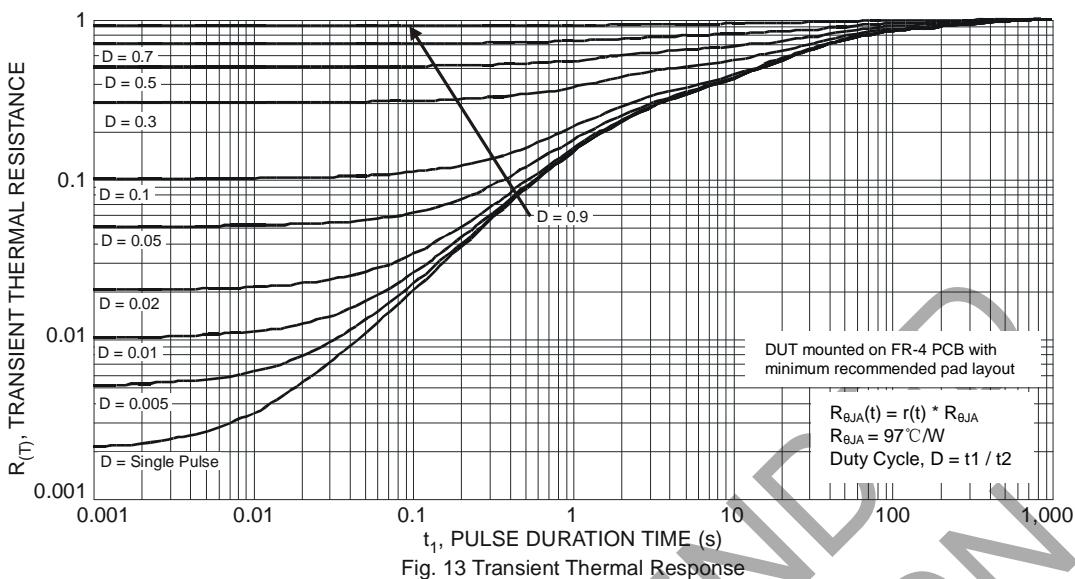


Fig. 12 SOA, Safe Operation Area

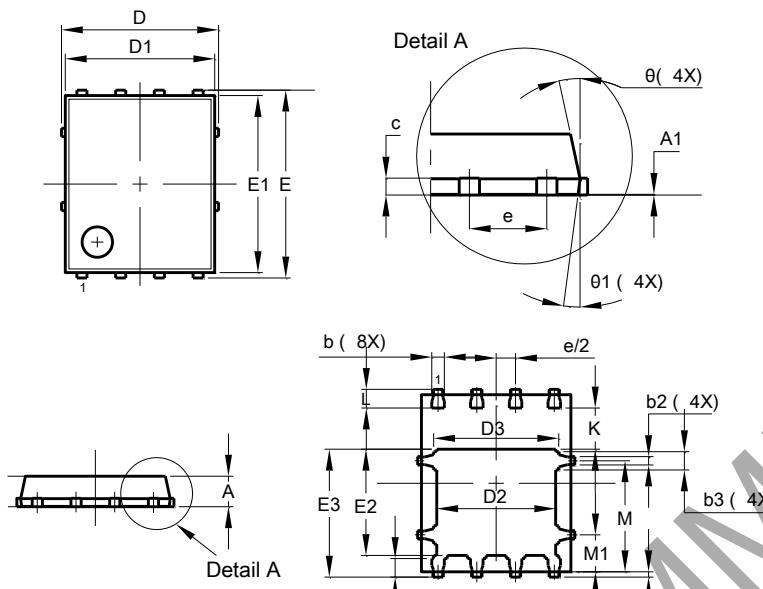


NOT RECOMMENDED  
FOR NEW DESIGN

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8

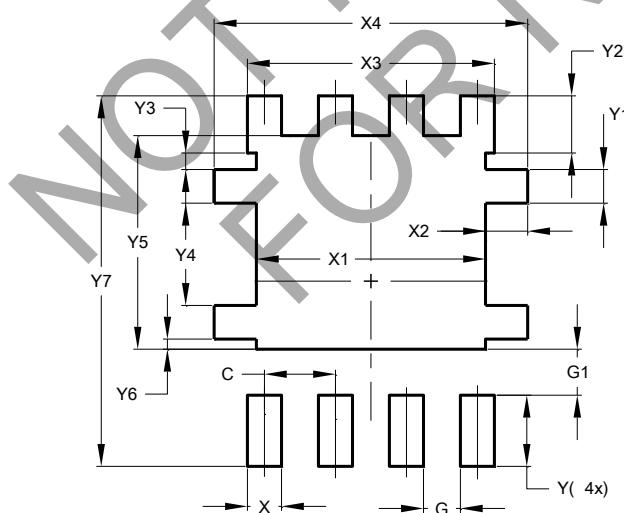


PowerDI5060-8			
Dim	Min	Max	Typ
<b>A</b>	0.90	1.10	1.00
<b>A1</b>	0.00	0.05	—
<b>b</b>	0.33	0.51	0.41
<b>b2</b>	0.200	0.350	0.273
<b>b3</b>	0.40	0.80	0.60
<b>c</b>	0.230	0.330	0.277
<b>D</b>	5.15 BSC		
<b>D1</b>	4.70	5.10	4.90
<b>D2</b>	3.70	4.10	3.90
<b>D3</b>	3.90	4.30	4.10
<b>E</b>	6.15 BSC		
<b>E1</b>	5.60	6.00	5.80
<b>E2</b>	3.28	3.68	3.48
<b>E3</b>	3.99	4.39	4.19
<b>e</b>	1.27 BSC		
<b>G</b>	0.51	0.71	0.61
<b>K</b>	0.51	—	—
<b>L</b>	0.51	0.71	0.61
<b>L1</b>	0.100	0.200	0.175
<b>M</b>	3.235	4.035	3.635
<b>M1</b>	1.00	1.40	1.21
<b>theta</b>	10°	12°	11°
<b>theta1</b>	6°	8°	7°
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
<b>C</b>	1.270
<b>G</b>	0.660
<b>G1</b>	0.820
<b>X</b>	0.610
<b>X1</b>	4.100
<b>X2</b>	0.755
<b>X3</b>	4.420
<b>X4</b>	5.610
<b>Y</b>	1.270
<b>Y1</b>	0.600
<b>Y2</b>	1.020
<b>Y3</b>	0.295
<b>Y4</b>	1.825
<b>Y5</b>	3.810
<b>Y6</b>	0.180
<b>Y7</b>	6.610

**IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

**LIFE SUPPORT**

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2017, Diodes Incorporated

[www.diodes.com](http://www.diodes.com)